

Martin Frentrup

List of Publications by Year in descending order

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citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Orientation control of GaN and grown on sapphire by metal-organic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 2171-2174. | 1.5 | 42 |
| 2 | Crystal orientation of GaN layers on (101 0) m -plane sapphire. Physica Status Solidi (B): Basic Research, 2011, 248, 583-587. | 1.5 | 42 |
| 3 | X-ray diffraction analysis of cubic zincblende III-nitrides. Journal Physics D: Applied Physics, 2017, 50, 433002. | 2.8 | 41 |
| 4 | Determination of lattice parameters, strain state and composition in semipolar III-nitrides using high resolution X-ray diffraction. Journal of Applied Physics, 2013, 114, . | 2.5 | 35 |
| 5 | Single phase $\text{Al}_{1-x}\text{In}_x\text{Ga}_{1-x}\text{N}$ heteroepitaxial templates grown on (111) sapphire. Journal of Crystal Growth, 2011, 331, 231-235. | 1.5 | 23 |
| 6 | Indium incorporation efficiency and critical layer thickness of (202 $\bar{1}$) InGaN layers on GaN. Applied Physics Letters, 2012, 101, . | 3.3 | 21 |
| 7 | Effect of growth temperature and V/III-ratio on the surface morphology of MOVPE-grown cubic zincblende GaN. Journal of Applied Physics, 2018, 124, . | 2.5 | 20 |
| 8 | Optimizing GaN (111) heteroepitaxial templates grown on (111) sapphire. Physica Status Solidi (B): Basic Research, 2016, 253, 61-66. | 1.5 | 19 |
| 9 | MOVPE growth of semipolar (111) AlGaInN heteroepitaxial templates on (111) sapphire. Journal of Crystal Growth, 2015, 411, 106-109. | 1.5 | 18 |
| 10 | Anisotropic optical properties of semipolar AlGaIn layers grown on m-plane sapphire. Applied Physics Letters, 2015, 106, . | 3.3 | 17 |
| 11 | Investigation of stacking faults in MOVPE-grown zincblende GaN by XRD and TEM. Journal of Applied Physics, 2019, 125, . | 2.5 | 17 |
| 12 | Low defect large area semipolar (112) GaN grown on patterned (113) silicon. Physica Status Solidi (B): Basic Research, 2015, 252, 1104-1108. | 1.5 | 16 |
| 13 | Ti Alloyed $\hat{\pm}$ -Ga ₂ O ₃ : Route towards Wide Band Gap Engineering. Micromachines, 2020, 11, 1128. | 2.9 | 16 |
| 14 | Growth and characterization of stacking fault reduced GaN (1,0,ar{1},3) on sapphire. Journal Physics D: Applied Physics, 2013, 46, 125308. | 2.8 | 12 |
| 15 | Polarization of photoluminescence emission from semi-polar (11 $\hat{\pm}$ 22) AlGaIn layers. Applied Physics Letters, 2014, 104, 051906. | 3.3 | 10 |
| 16 | Defect structures in (001) zincblende GaN/3C-SiC nucleation layers. Journal of Applied Physics, 2021, 129, . | 2.5 | 10 |
| 17 | Multimicroscopy of cross-section zincblende GaN LED heterostructure. Journal of Applied Physics, 2021, 130, . | 2.5 | 6 |
| 18 | X-ray reflectivity method for the characterization of InGaIn/GaN quantum well interface. Physica Status Solidi (B): Basic Research, 2017, 254, 1600664. | 1.5 | 5 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Investigation of MOVPE-grown zincblende GaN nucleation layers on 3C-SiC/Si substrates. Journal of Crystal Growth, 2019, 524, 125167. | 1.5 | 5 |
| 20 | Defect characterization of {101 $\bar{1}$ 3} GaN by electron microscopy. Journal of Applied Physics, 2022, 131, . | 2.5 | 5 |
| 21 | X-ray characterisation of the basal stacking fault densities of (112 $\bar{1}$,2) GaN. CrystEngComm, 2021, 23, 6059-6069. | 2.6 | 4 |
| 22 | Influence of Al _x Ga _{1-x} N nucleation layers on MOVPE-grown zincblende GaN epilayers on 3C-SiC/Si(001). Journal Physics D: Applied Physics, 2022, 55, 175110. | 2.8 | 4 |
| 23 | Facet analysis of truncated pyramid semi-polar GaN grown on Si(100) with rare-earth oxide interlayer. Journal of Applied Physics, 2016, 120, 105301. | 2.5 | 3 |
| 24 | Investigation of wurtzite formation in MOVPE-grown zincblende GaN epilayers on Al _x Ga _{1-x} N nucleation layers. Journal of Applied Physics, 2022, 131, . | 2.5 | 3 |
| 25 | Waveguide Optimization for Semipolar (In,Al,Ga)N Lasers. Japanese Journal of Applied Physics, 2013, 52, 08JG12. | 1.5 | 2 |
| 26 | Nanoscale structural and chemical analysis of F-implanted enhancement-mode InAlN/GaN heterostructure field effect transistors. Journal of Applied Physics, 2018, 123, 024902. | 2.5 | 2 |
| 27 | Effect of electron blocking layers on the conduction and valence band profiles of InGaN/GaN LEDs. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 262-265. | 0.8 | 1 |